

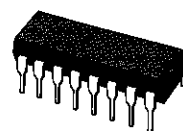
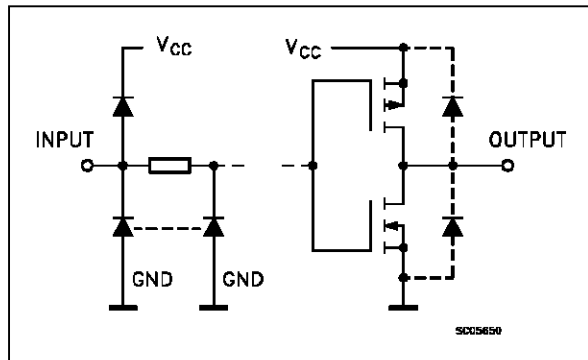
8 BIT SIPO SHIFT REGISTER

- **HIGH SPEED**
 $t_{PD} = 14 \text{ ns (TYP.) AT } V_{CC} = 5 \text{ V}$
- **LOW POWER DISSIPATION**
 $I_{CC} = 4 \mu\text{A (MAX.) AT } T_A = 25^\circ\text{C } 6 \text{ V}$
- **HIGH NOISE IMMUNITY**
 $V_{NIH} = V_{NIL} = 28 \% V_{CC} \text{ (MIN.)}$
- **OUTPUT DRIVE CAPABILITY**
 10 LSTTL LOADS
- **SYMMETRICAL OUTPUT IMPEDANCE**
 $|I_{OH}| = I_{OL} = 4 \text{ mA (MIN.)}$
- **BALANCED PROPAGATION DELAYS**
 $t_{PLH} = t_{PHL}$
- **WIDE OPERATING VOLTAGE RANGE**
 $V_{CC} \text{ (OPR)} = 2 \text{ V TO } 6 \text{ V}$
- **PIN AND FUNCTION COMPATIBLE WITH**
 54/74LS251

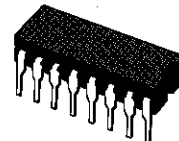
DESCRIPTION

The M54/74HC251 is a high speed CMOS 8-CHANNEL MULTIPLEXER (3-STATE) fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. This multiplexer features both true (Y) and complement (W) outputs as well as STROBE input. The STROBE must be a low logic level to enable this device. When the STROBE input is high, both outputs are in the high impedance state. When enabled, address information on the data select inputs determines which data input is routed to Y and W. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



B1R
(Plastic Package)



F1R
(Ceramic Package)



M1R
(Micro Package)

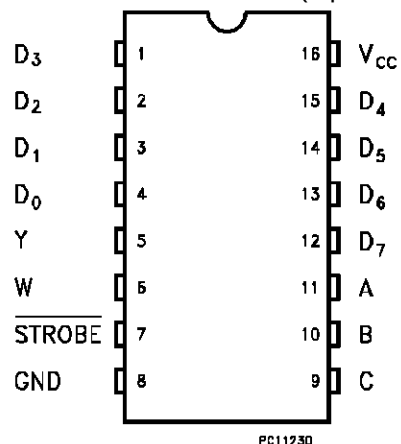


C1R
(Chip Carrier)

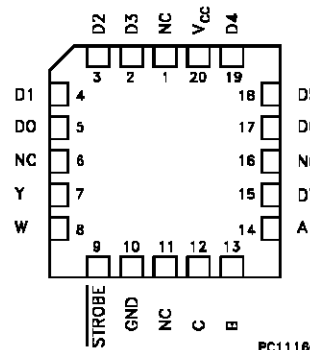
ORDER CODES :

M54HC251F1R	M74HC251M1R
M74HC251B1R	M74HC251C1R

PIN CONNECTIONS (top view)



PC11230



NC =
No Internal
Connection

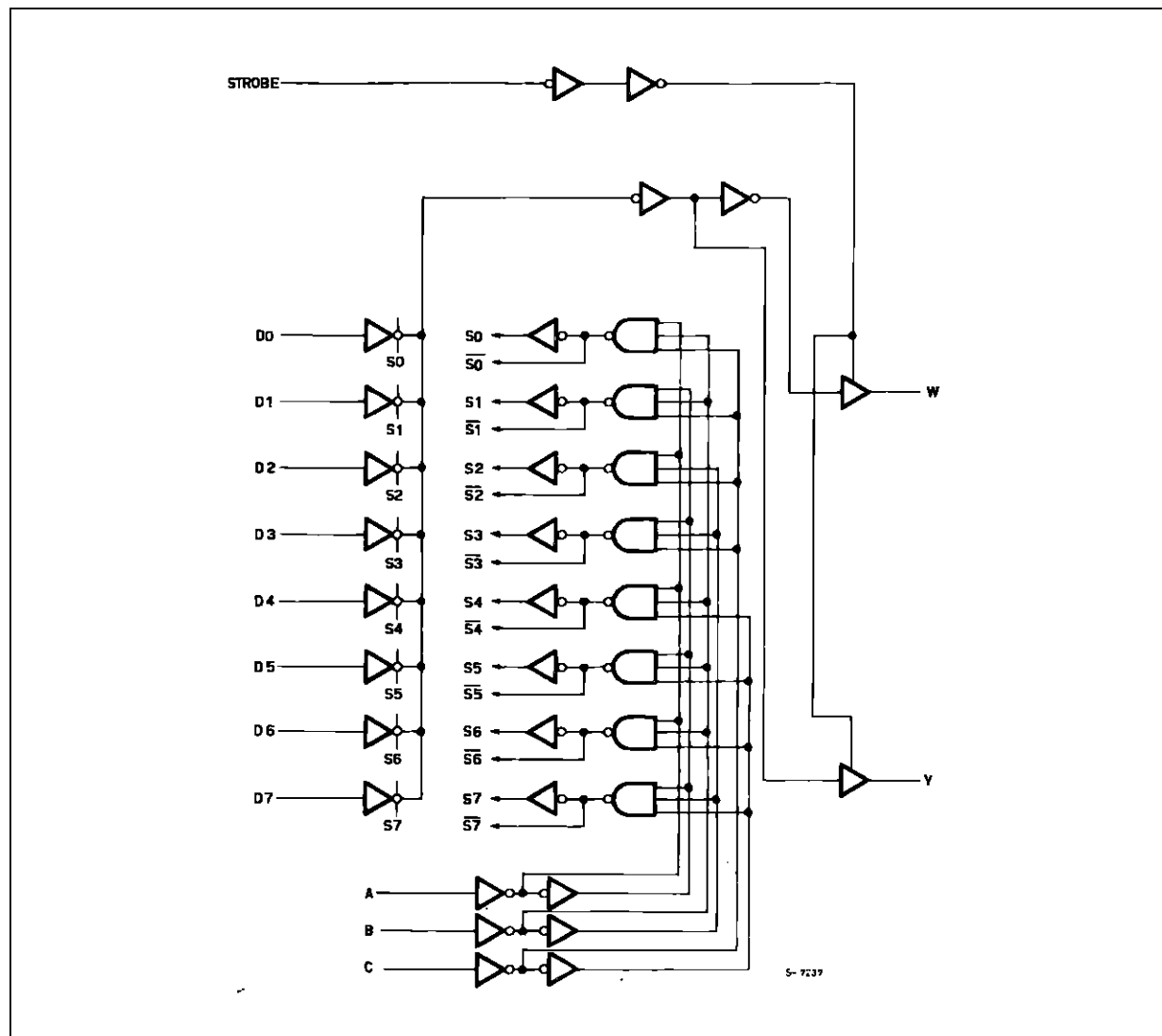
PC11180

TRUTH TABLE

INPUTS				OUTPUTS	
C	B	A	STROBE $\overline{S}$	Y	W
X	X	X	H	Z	Z
L	L	L	L	D0	$\overline{D0}$
L	L	H	L	D1	$\overline{D1}$
L	H	L	L	D2	$\overline{D2}$
L	H	H	L	D3	$\overline{D3}$
H	L	L	L	D4	$\overline{D4}$
H	L	H	L	D5	$\overline{D5}$
H	H	L	L	D6	$\overline{D6}$
H	H	H	L	D7	$\overline{D7}$

X: Don't Care Z: HIGH Impedance

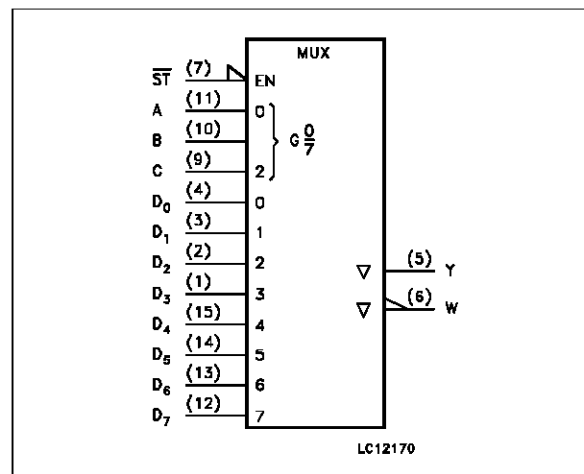
LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
4, 3, 2, 1, 15, 14, 13, 12	D0 to D7	Multiplexer Inputs
5	Y	Multiplexer Output
6	W	Complementary Multiplexer Output
7	$\overline{\text{STROBE}}$	3 State Output Enable Input
11, 10, 9	A, B, C	Select Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage		2 to 6	V
V _I	Input Voltage		0 to V _{CC}	V
V _O	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C °C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		V _{CC} = 4.5 V	0 to 500	
		V _{CC} = 6 V	0 to 400	

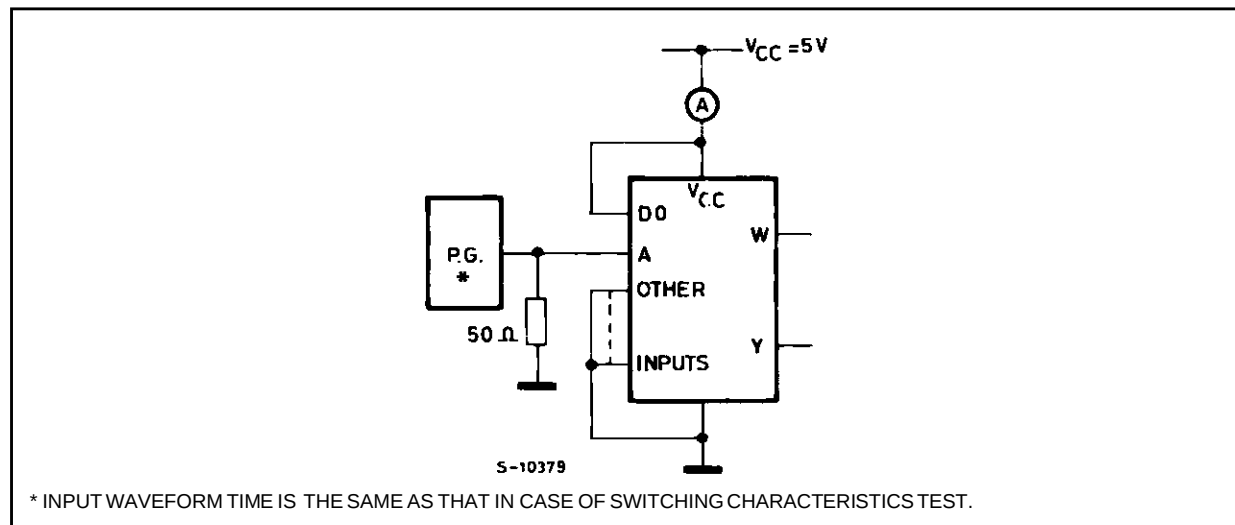
DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value						Unit		
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V	
		4.5		3.15			3.15		3.15			
		6.0		4.2			4.2		4.2			
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V	
		4.5				1.35		1.35		1.35		
		6.0				1.8		1.8		1.8		
V _{OH}	High Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O =-20 μA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = 20 μA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1		±1	μA	
I _{OZ}	3 State Output Off State Current	6.0	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.5		±5.0		±10	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	μA	

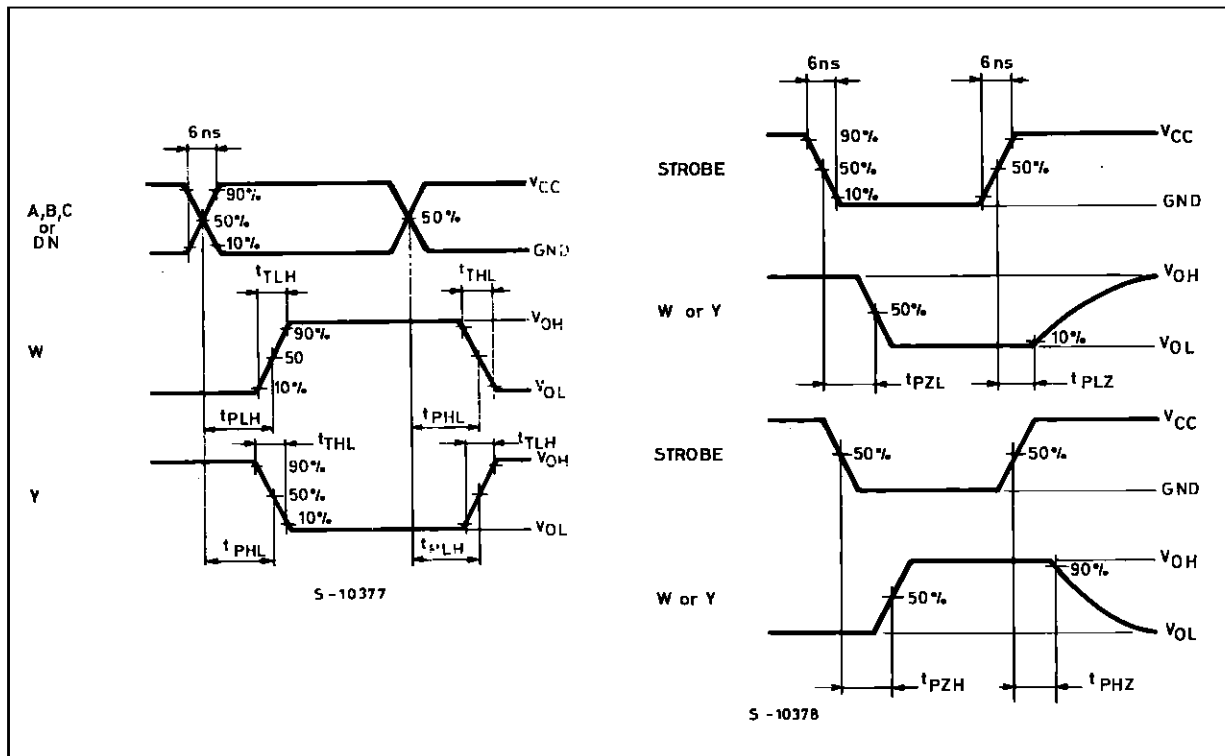
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay Time (D - Y, W)	2.0			64	130		165		195	ns
		4.5			16	26		33		39	
		6.0			14	22		28		33	
t _{PLH} t _{PHL}	Propagation Delay Time (A, B, C - Y, W)	2.0			80	160		200		240	ns
		4.5			20	32		40		48	
		6.0			17	27		34		41	
t _{PZL} t _{PZH}	Output Enable Time	2.0	R _L = 1 KΩ		36	90		115		135	ns
		4.5			11	18		23		27	
		6.0			9	15		20		23	
t _{PLZ} t _{PHZ}	Output Disable Time	2.0	R _L = 1 KΩ		26	85		105		130	ns
		4.5			13	17		21		26	
		6.0			11	14		18		22	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				62						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

TEST WAVEFORM I_{CC} (Opr.)

SWITCHING CHARACTERISTICS TEST WAVEFORM



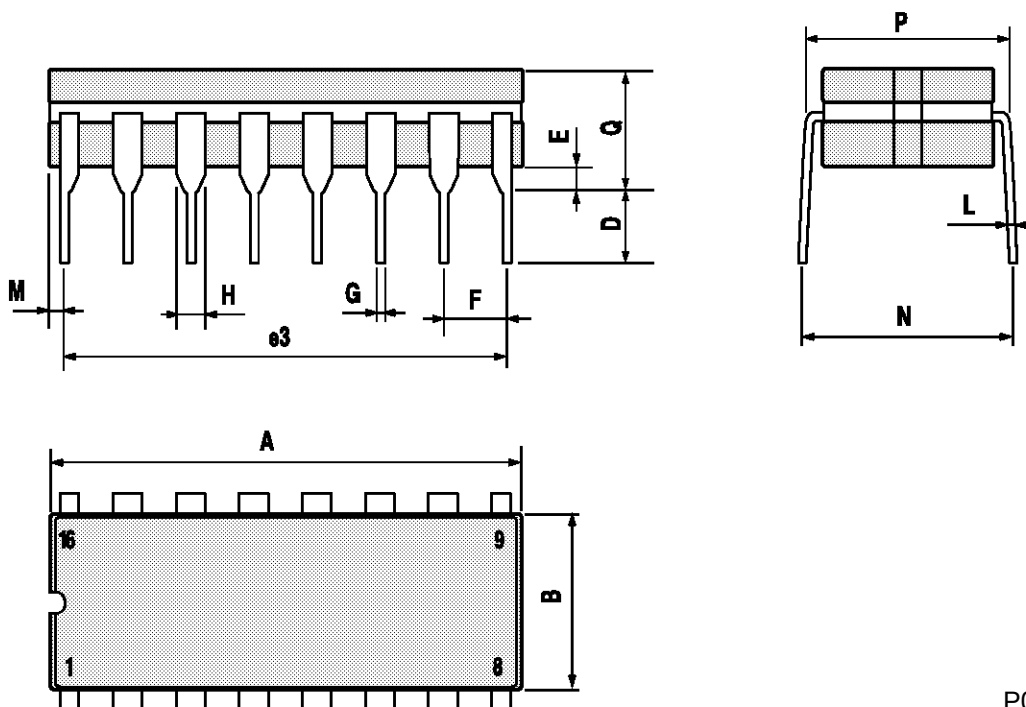
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



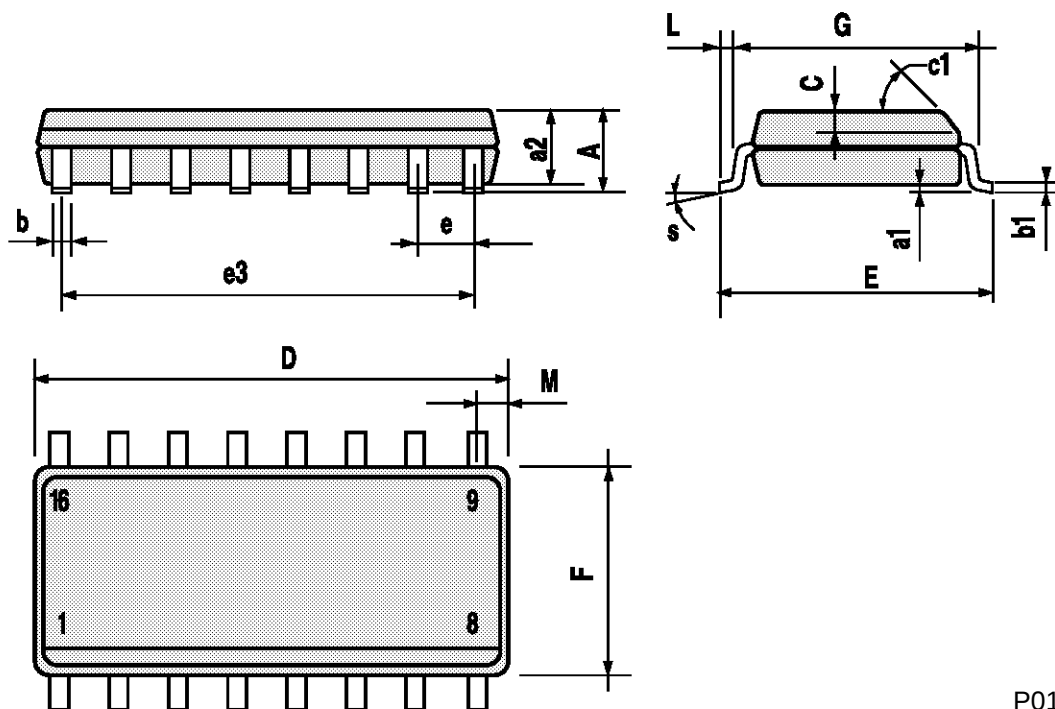
Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A